

94 8583

FEATURES

- Package type: leaded
- Package form: top view
- Dimensions (L x W x H in mm): 5.4 x 4.3 x 3.2
- Radiant sensitive area (in mm²): 7.5
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 65^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

RoHS
COMPLIANT**DESCRIPTION**

BPW34 is a PIN photodiode with high speed and high radiant sensitivity in miniature, flat, top view, clear plastic package. It is sensitive to visible and near infrared radiation.

BPW34S is packed in tubes, specifications like BPW34.

APPLICATIONS

- High speed photo detector

PRODUCT SUMMARY

COMPONENT	I_{ra} (μA)	φ (deg)	$\lambda_{0.1}$ (nm)
BPW34	50	± 65	430 to 1100
BPW34S	50	± 65	430 to 1100

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW34	Bulk	MOQ: 3000 pcs, 3000 pcs/bulk	Top view
BPW34S	Tube	MOQ: 1800 pcs, 45 pcs/tube	Top view

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	215	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 3$ s	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	350	K/W

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 100 \mu A, E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10 V, E = 0$	I_{ro}		2	30	nA
Diode capacitance	$V_R = 0 V, f = 1 \text{ MHz}, E = 0$	C_D		70		pF
	$V_R = 3 V, f = 1 \text{ MHz}, E = 0$	C_D		25	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	V_o		350		mV
Temperature coefficient of V_o	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{V_o}		- 2.6		mV/K
Short circuit current	$E_A = 1 \text{ klx}$	I_k		70		μA
	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I_k		47		μA
Temperature coefficient of I_k	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{I_k}		0.1		%/K
Reverse light current	$E_A = 1 \text{ klx}, V_R = 5 V$	I_{ra}		75		μA
	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 V$	I_{ra}	40	50		μA
Angle of half sensitivity		ϕ		± 65		deg
Wavelength of peak sensitivity		λ_p		900		nm
Range of spectral bandwidth		$\lambda_{0.1}$		430 to 1100		nm
Noise equivalent power	$V_R = 10 V, \lambda = 950 \text{ nm}$	NEP		4×10^{-14}		W/ $\sqrt{\text{Hz}}$
Rise time	$V_R = 10 V, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_r		100		ns
Fall time	$V_R = 10 V, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_f		100		ns

Note

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BASIC CHARACTERISTICS

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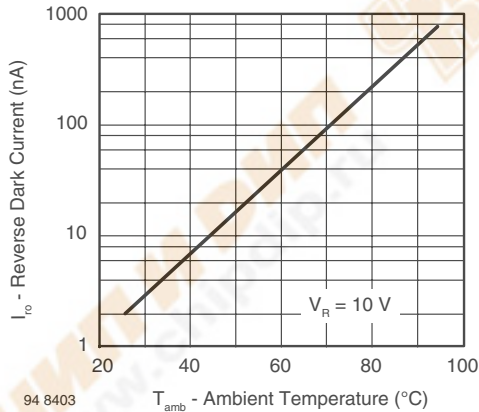


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

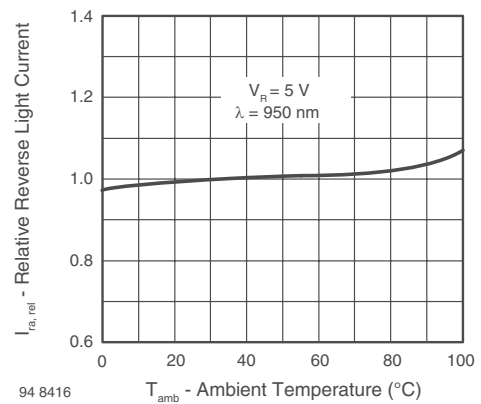


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

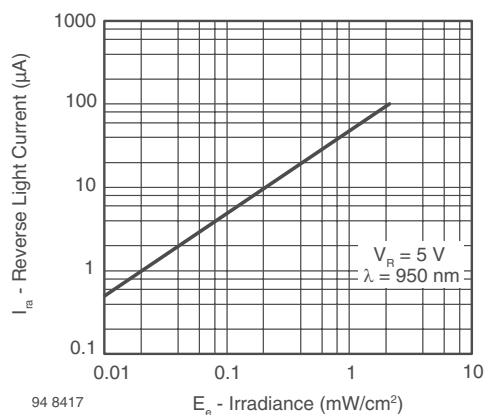


Fig. 3 - Reverse Light Current vs. Irradiance

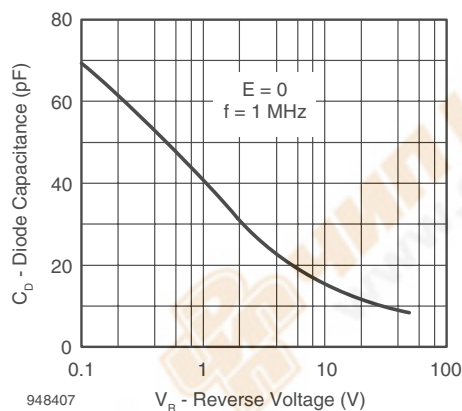


Fig. 6 - Diode Capacitance vs. Reverse Voltage

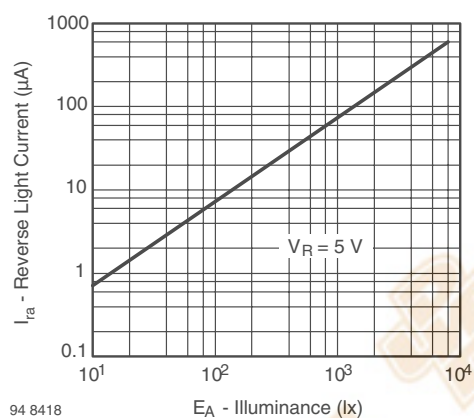


Fig. 4 - Reverse Light Current vs. Illuminance

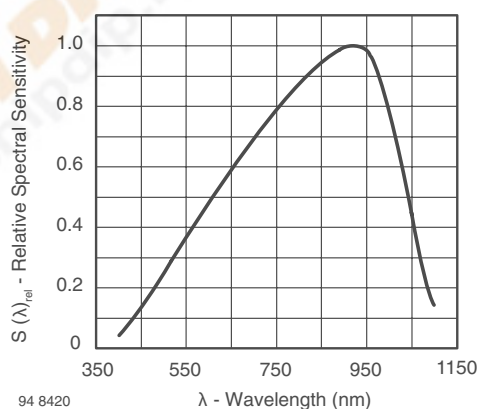


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

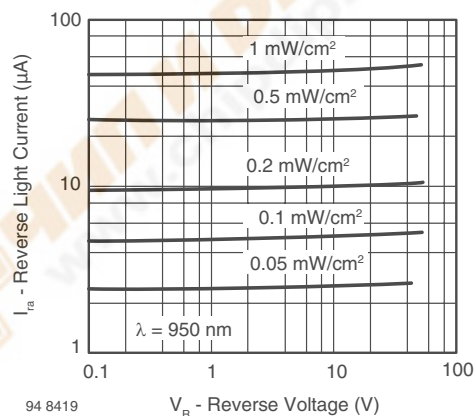


Fig. 5 - Reverse Light Current vs. Reverse Voltage

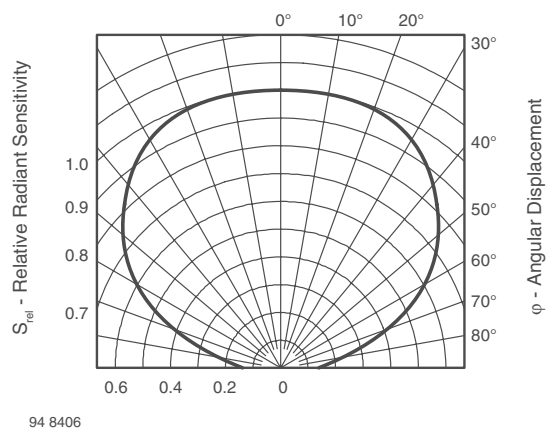
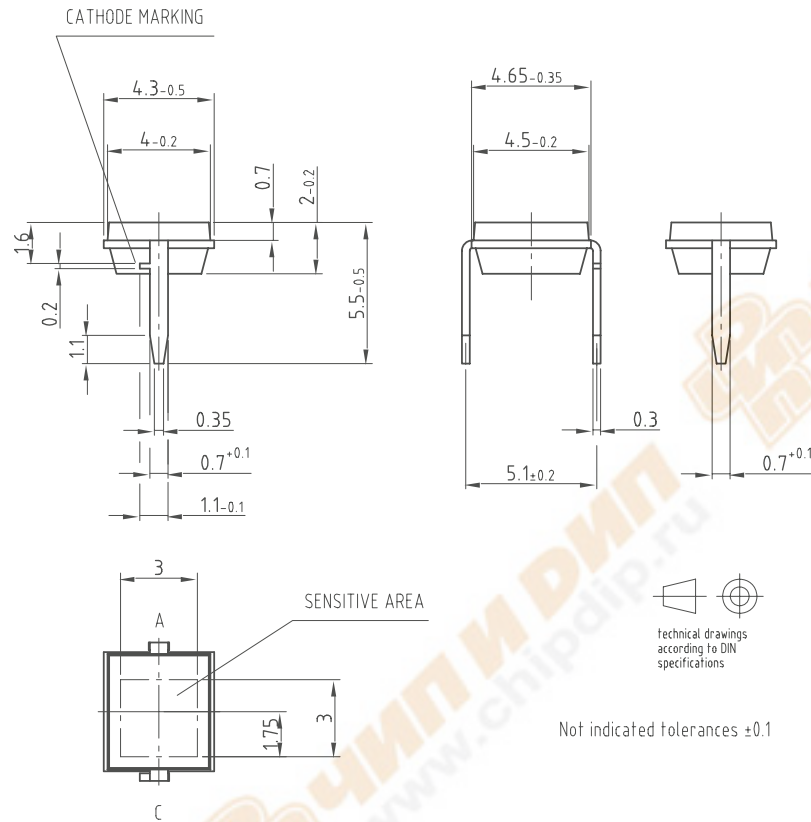


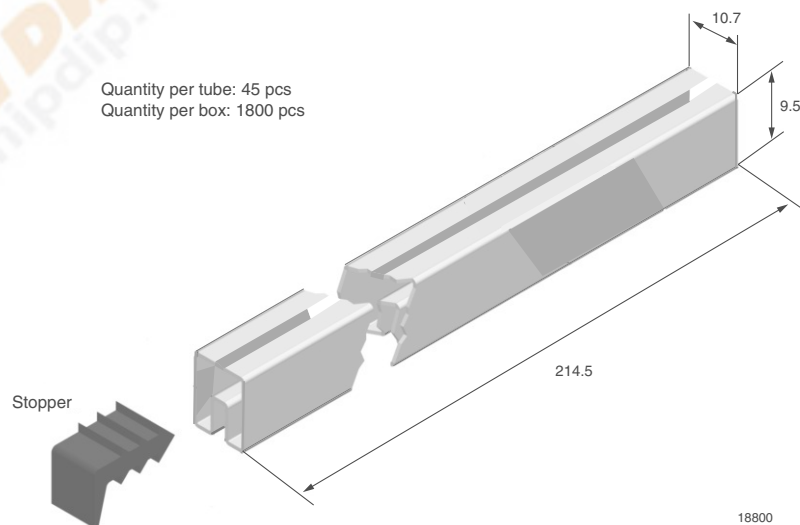
Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters

Drawing-No.: 6.544-5315.01-4

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TUBE PACKAGING DIMENSIONS in millimeters

18800

Fig. 9 - Drawing Proportions not scaled